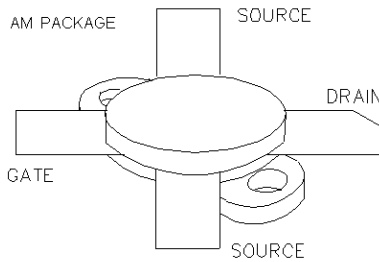




**General Description**

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"<sup>TM</sup> process features gold metal for greatly extended lifetime. Low output capacitance and high  $F_t$  enhance broadband performance



**PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR**

**125 Watts Single Ended**

**Package Style AM**

**HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE**

**ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)**

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
250 Watts	0.7 °C/W	200 °C	-65 °C to 150 °C	12 A	70 V	70V	30V

**RF CHARACTERISTICS ( 125WATTS OUTPUT )**

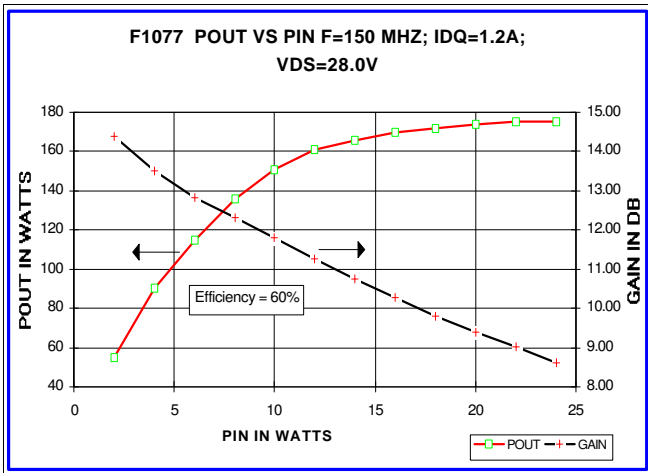
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	11			dB	$I_{dq} = 1.2 A, V_{ds} = 28.0V, F = 150 MHz$
$\eta$	Drain Efficiency		60		%	$I_{dq} = 1.2 A, V_{ds} = 28.0V, F = 150 MHz$
VSWR	Load Mismatch Tolerance			20:1	Relative	$I_{dq} = 1.2 A, V_{ds} = 28.0V, F = 150 MHz$

**ELECTRICAL CHARACTERISTICS (EACH SIDE)**

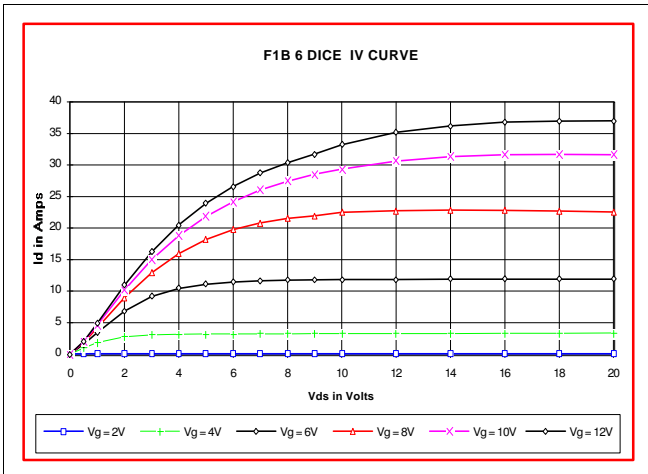
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	$I_{ds} = 0.3 A, V_{gs} = 0V$
Idss	Zero Bias Drain Current			6	mA	$V_{ds} = 28.0 V, V_{gs} = 0V$
Igss	Gate Leakage Current			1	uA	$V_{ds} = 0 V, V_{gs} = 30V$
Vgs	Gate Bias for Drain Current	1		7	V	$I_{ds} = 0.6 A, V_{gs} = V_{ds}$
gM	Forward Transconductance		4.8		Mho	$V_{ds} = 10V, V_{gs} = 5V$
Rdson	Saturation Resistance		0.18		Ohm	$V_{gs} = 20V, I_{ds} = 24A$
Idsat	Saturation Current		33		Amp	$V_{gs} = 20V, V_{ds} = 10V$
Ciss	Common Source Input Capacitance		198		pF	$V_{ds} = 28.0 V, V_{gs} = 0V, F = 1 MHz$
Crss	Common Source Feedback Capacitance		24		pF	$V_{ds} = 28.0 V, V_{gs} = 0V, F = 1 MHz$
Coss	Common Source Output Capacitance		120		pF	$V_{ds} = 28.0 V, V_{gs} = 0V, F = 1 MHz$

# F1077

POUT VS PIN GRAPH

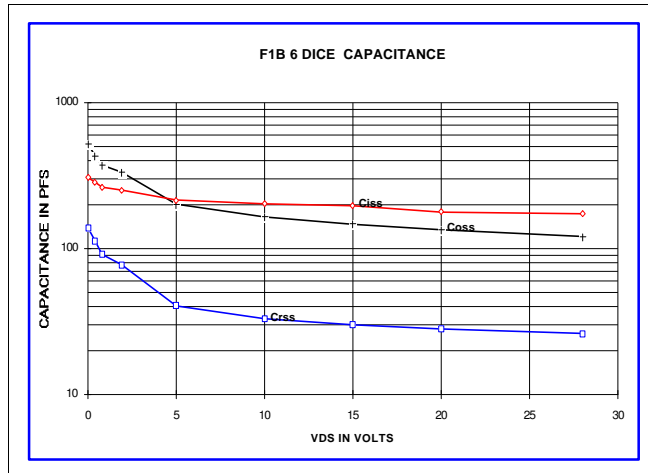


IV CURVE

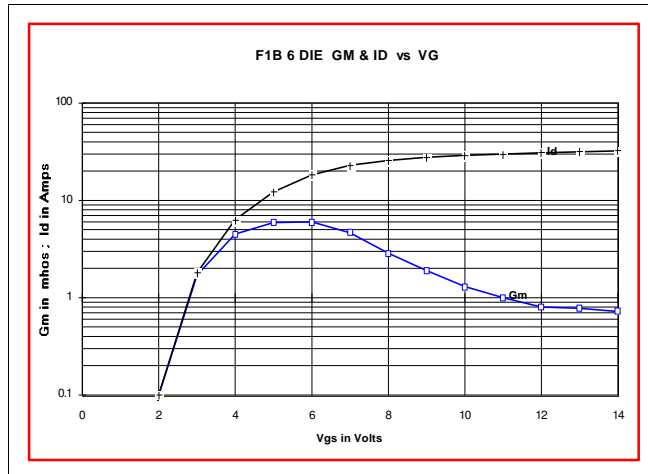


IV CURVE

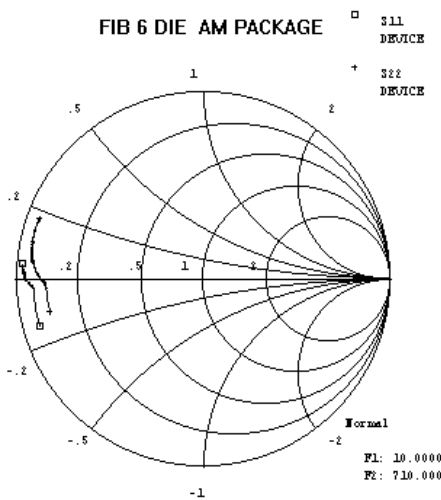
CAPACITANCE VS VOLTAGE



ID AND GM VS VGS



S11 AND S22 SMITH CHART



PACKAGE DIMENSIONS IN INCHES

